



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	Rds(on) Max	I _D Max T _C = +25°C
001/	42mΩ @ V _{GS} = -10V	-19.9A
-30V	65mΩ @ V _{GS} = -4.5V	-16A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power management functions
- DC-DC converters

Features and Benefits

- Low Rds(ON) Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES[™] DMP3045LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

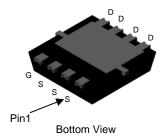
Mechanical Data

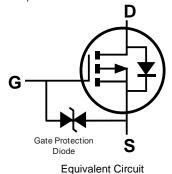
- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over copper Leadframe.
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)





Top View





Ordering Information (Note 4)

Part Number	Packago	Packing		
Fait Number	Package	Qty.	Carrier	
DMP3045LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel	
DMP3045LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel	

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



S3W = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 22 = 2022)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	-30	V
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	lo	-5.7 -4.6	Α
Continuous Drain Current (Note 7) $V_{GS} = -10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +70^{\circ}C$		lo	-19.9 -15.9	А	
Maximum Continuous Body Diode Forward Current (Note 7)			Is	-1.3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-76	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-76	Α
Avalanche Current (Note 8) L = 1mH			las	-7.8	А
Avalanche Energy (Note 8) L = 1mH			Eas	30.8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	135	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Reja	61	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	5	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage		-30	_		V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current		_	_	-1	μΑ	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	Descent	_	25	42	mΩ	$V_{GS} = -10V, I_{D} = -4.9A$	
Static Dialii-Source Off-Resistance	Rds(on)	_	43	65	mΩ	$V_{GS} = -4.5V$, $I_{D} = -3.7A$	
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	782	_	pF	45)/)/ 0)/	
Output Capacitance	Coss	_	110	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	74	_	pF		
Gate Resistance	Rg	_	10.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	6.6	_	nC		
Total Gate Charge (VGS = -10V)	Qg	_	13.6	_	nC	\/ 45\/ I- 40A	
Gate-Source Charge	Qgs	_	2.1	_	nC	$V_{DS} = -15V, I_{D} = -4.9A$	
Gate-Drain Charge	Qgd		2.7	_	nC	1	
Turn-On Delay Time	td(on)	_	4.1	_	ns		
Turn-On Rise Time	t _R	_	6.1	_	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	tD(OFF)	_	24.6	_	ns	$I_D = -4.9A, R_G = 6\Omega$	
Turn-Off Fall Time	tF	_	13.1	_	ns	1	
Reverse Recovery Time	t _{RR}	_	12.7	_	ns		
Reverse Recovery Charge	Qrr	_	4.8	_	nC	Is = -11.5A, dI/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

^{7.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.



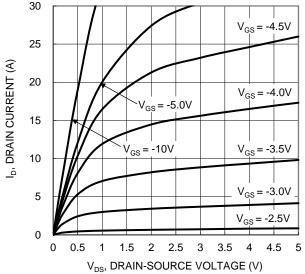


Figure 1. Typical Output Characteristic

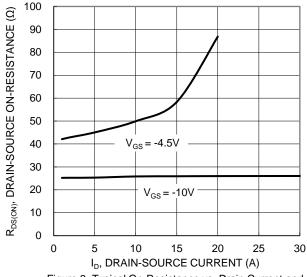


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

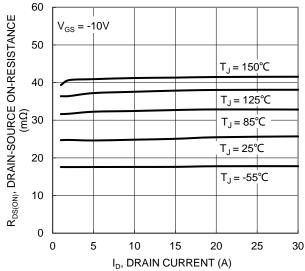


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

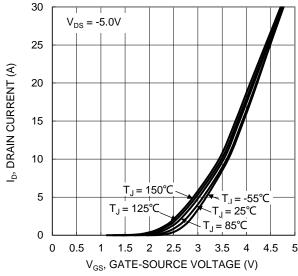


Figure 2. Typical Transfer Characteristic

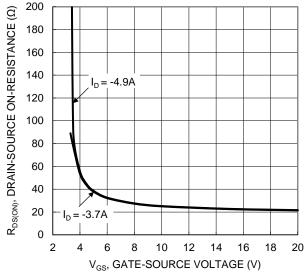


Figure 4. Typical Transfer Characteristic

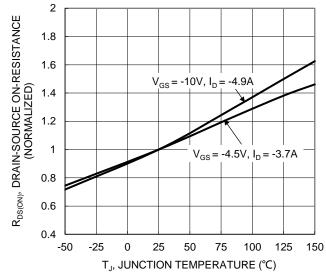


Figure 6. On-Resistance Variation with Temperature



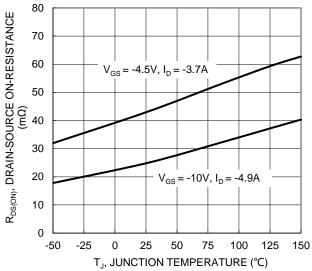


Figure 7. On-Resistance Variation with Temperature

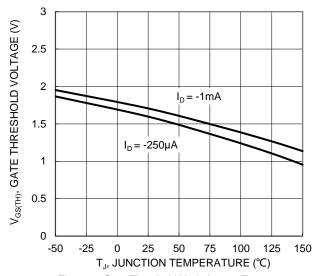


Figure 8. Gate Threshold Variation vs. Temperature

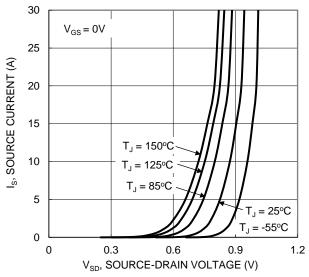


Figure 9. Diode Forward Voltage vs. Current

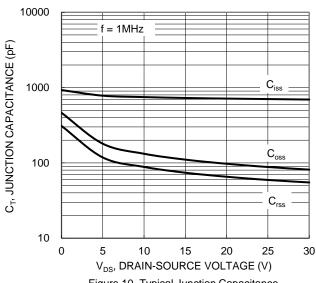
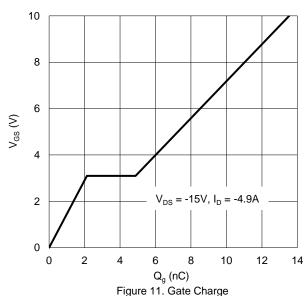


Figure 10. Typical Junction Capacitance



Single Pulse DC DUT on Infinite Heatsink 0.1 0.1 10 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

100

10

ID, DRAIN CURRENT (A)

R_{DS(ON)}

 $T_{J(Max)} = 150^{\circ}C$ T_C = 25 °C

100



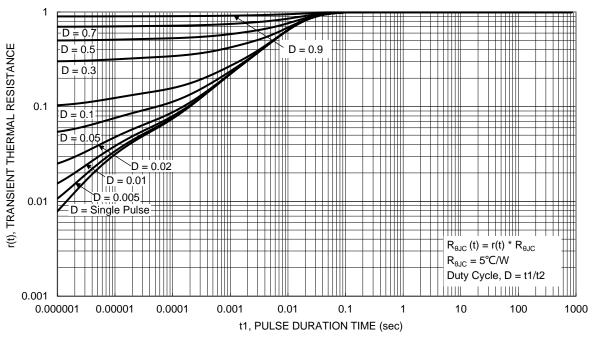


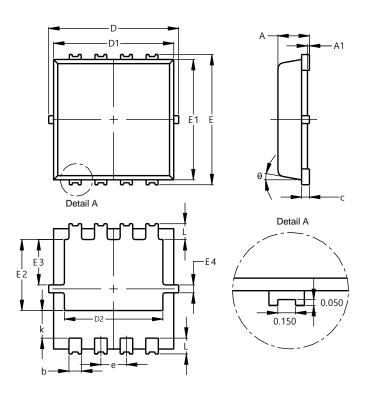
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

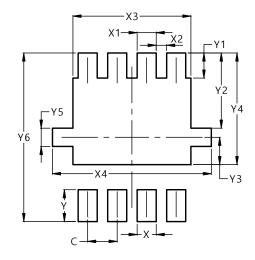


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Min Max				
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	-	-	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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